

## **isc** Silicon PNP Power Transistors

# D45C5

#### DESCRIPTION

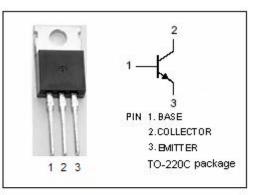
- Low Saturation Voltage
- Good Linearity of h<sub>FE</sub>
- Fast Switching Speeds
- Complement to Type D44C5
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

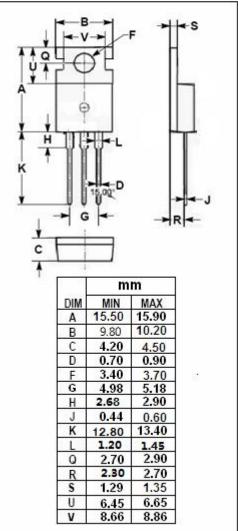
### **APPLICATIONS**

 Designed for various specific and general purpose application such as: output and driver stages of amplifiers operating at frequencies from DC to greater than 1.0MHz series, shunt and switching regulators; low and high frequency inverters/ converters and many others.

SYMBOL	PARAMETER		ALUE	UNIT	
V <sub>CES</sub>	Collector-Emitter Voltage	ctor-Emitter Voltage -55		V	
V <sub>CEO</sub>	Collector-Emitter Voltage		-45	V	
Vebo	Emitter-Base Voltage -5		-5	V	
Ic	Collector Current-Continuous	-4		A	
I <sub>CM</sub>	Collector Current-Peak		-6	А	
Iв	Base Current-Continuous	-1		А	
Pc	Collector Power Dissipation @Tc=25°C	30		W	
Tj	Junction Temperature	150		°C	
T <sub>stg</sub>	Storage Temperature Range	-55~150		°C	
THERMAL	CHARACTERISTICS				
SYMBOL	PARAMETER			UNIT	
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	4.2	°C/W		

### ABSOLUTE MAXIMUM RATINGS(Ta=25℃)





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### **ELECTRICAL CHARACTERISTICS**

#### T<sub>c</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -1A; I <sub>B</sub> = -50mA			-0.5	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = -1A; I <sub>B</sub> = -100mA			-1.3	V
I <sub>CES</sub>	Collector Cutoff Current	V <sub>CE</sub> = -55V, V <sub>BE</sub> = 0			-10	μA
Іево	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> = 0			-100	μA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = -0.2A; V <sub>CE</sub> = -1V	40		120	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = -1A; V <sub>CE</sub> = -1V	20			
fT	Current-Gain—Bandwidth Product	I <sub>C</sub> = -20mA;V <sub>CE</sub> = -4V;f <sub>test</sub> = 1MHz		40		MHz

Switching Times

tr	Rise Time			0.2	μs
ts	Storage Time	I <sub>C</sub> = -1A; I <sub>B1</sub> = -I <sub>B2</sub> = -0.1A; V <sub>CC</sub> = -20V		0.6	μs
tr	Fall Time			0.3	μ <b>S</b>

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